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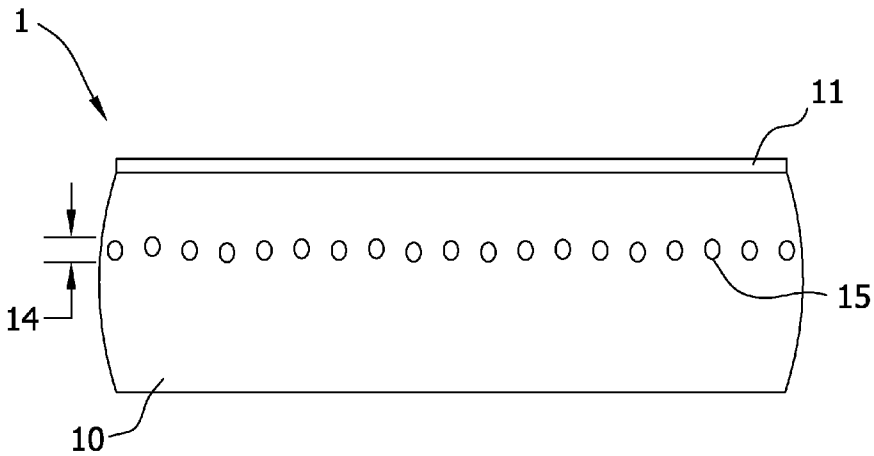
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(54) Title: DIFFUSION CONTROL IN HEAVILY DOPED SUBSTRATES

FIG. 1



(57) Abstract: This invention generally relates to a process for suppressing silicon self-interstitial diffusion near the substrate/epitaxial layer interface of an epitaxial silicon wafer having a heavily doped silicon substrate and a lightly doped silicon epitaxial layer. Interstitial diffusion into the epitaxial layer is suppressed by a silicon self-interstitial sink layer comprising dislocation loops.

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